

Plastic-Encapsulate Transistors

TRANSISTOR (NPN)

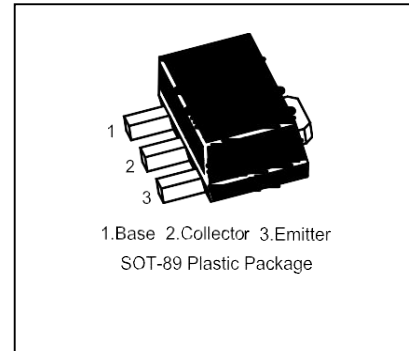
FEATURES

- Compliment to SS8550

MARKING: Y1

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1.5	A
P_C	Collector Power dissipation	0.5	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	$^{\circ}\text{C}/\text{W}$
T_J	Storage Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1\text{mA}, I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{CEO}	$V_{CE}=20\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	120		400	
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=800\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=800\text{mA}, I_B=80\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=800\text{mA}, I_B=80\text{mA}$			1.2	V
Base-emitter voltage	V_{BE}	$V_{CE}=1\text{V}, I_C=10\text{mA}$			1	V
Base-emitter positive forward voltage	V_{BEF}	$I_B=1\text{A}$			1.55	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=30\text{MHz}$	100			MHz
output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$			15	pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	C	D	D1	D2
Range	120-200	160-300	200-350	300-400

